

**C735-40P2**

Infrared LED CHIP

<Specifications>

| Commodity Type and Physical Characteristics |                    |
|---|--------------------|
| Material                                    | GaAlAs/GaAlAs(DDH) |
| Top Side N(cathode)side                     | Au Alloy/Pad       |
| Bottom Side P(anode)side                    | Au Alloy           |
| Electrode Pattern                           | Fig.1              |
| Chip Size                                   | Fig.2              |
| Chip Thickness                              | Fig.2              |
| Emission Area                               | Fig.2              |

| Electro-Optical Characteristics [Ta=25°C] |                 |           |      |      |      |      |
|---|-----------------|-----------|------|------|------|------|
| Item                                      | Symbol          | Condition | Min. | Typ. | Max. | Unit |
| Forward Voltage                           | Vf              | IF=20mA   |      | 1.7  | 1.9  | V    |
| Reverse Current                           | IR              | VR=5V     |      |      | 10   | uA   |
| Power Intensity                           | PO              | IF=20mA   | 2.0  | 3.5  |      | mW   |
| Peak Wavelength                           | $\lambda P$     | IF=20mA   | 720  | 735  | 750  | nm   |
| Spectral Radiation Bandwidth              | $\Delta\lambda$ | IF=20mA   |      | 30   |      | nm   |
| Rise Time                                 | tr              | IF=20mA   |      | 80   |      | ns   |
| Fall Time                                 | tf              | IF=20mA   |      | 80   |      | ns   |

Die shall be mounted on TO-18 gold header without resin coated.

[Unit:um]

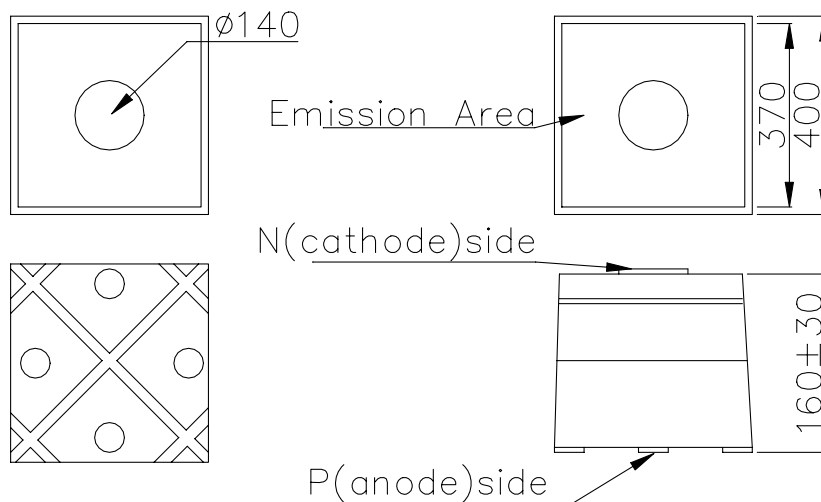


Fig.1 Electrode Pattern

Fig.2 Chip Size and Emission Area